

ABSTRACT OF THE DISCLOSURE

A plasma processing apparatus having 90 % or more of a side wall of an inner wall 101 of a reaction chamber 1 covered with a dielectric 102, and equipped with an earthed conductive member 21a having an area of less than 10 % of the side wall area of the inner wall 101 and having a structure to allow direct current from a plasma to flow therein, wherein the DC earth formed of the conductive member 21 is located at a position where floating potential of plasma (or plasma density) is higher than the floating potential of plasma 9 located near a wafer holding electrode 14 where there is relatively large wall chipping.